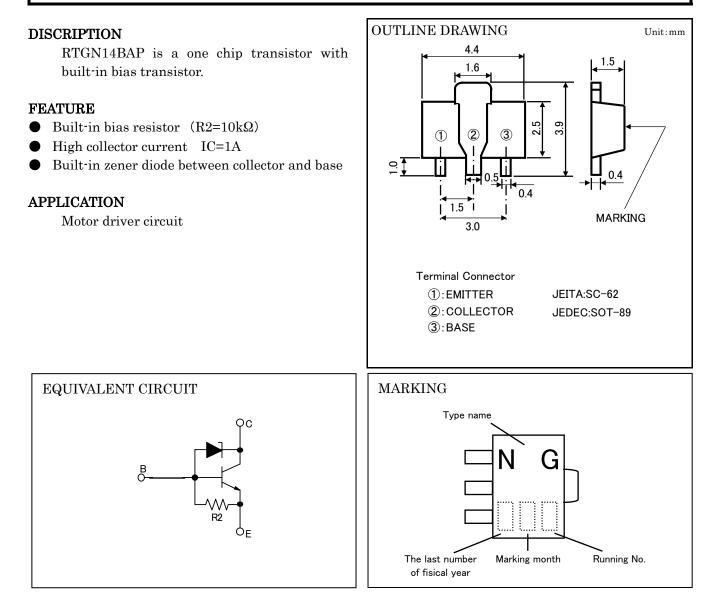
⟨SMALL-SIGNAL TRANSISTOR⟩

RTGN14BAP

TRANSISTOR WITH RESISTOR FOR SWITHING APPLICATION SILICON NPN EPITAXIAL TYPE



MAXIMUM RATING(Ta=25°C)

SYMBOL	PARAMETER	RATING	UNIT
$V_{\rm CBO}$	Collector to Base voltage	60±10	V
$V_{\rm EBO}$	Emitter to Base voltage	10	V
Vceo	Collector to Emitter voltage	60±10	V
$I_{\rm C}$	Collector current (DC)	1	А
Icm	Collector current (pulse)	2	А
Pc	Collector dissipation	500	mW
T_{j}	Junction temperature	+150	°C
$\mathrm{T}_{\mathrm{stg}}$	Storage temperature	-55~+150	°C

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TRANSISTOR WITH RESISTOR FOR SWITHING APPLICATION SILICON NPN EPITAXIAL TYPE

ELECTRICAL CHARACTERISTICS (Ta=25°C)

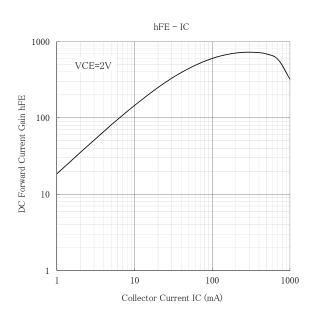
Symbol	Parameter	Test conditions	Limits			Unit
Symbol	Farameter	lest conditions		Тур	Max	Unit
Icbo	Collector cut off current	V _{CB} =40V, I _E =0		I	0.1	μA
VIL	Input voltage (OFF)	$V_{CE}=5V$, $I_{C}=100 \mu A$	0.3			V
hFE1	DC forward current gain	V _{CE} =2V, I _C =0.1A	200	I		—
hFE2	DC forward current gain	V _{CE} =2V, I _C =0.5A	300	I	I	—
hFE3	DC forward current gain	$V_{CE}=2V$, $I_{C}=1A$	200		-	_
$V_{\rm CE(sat)}$	C to E saturation voltage	Ic=500mA,IB=5mA	_	_	400	mV
R2	Emitter – Base resistor	—	7	10	13	kΩ

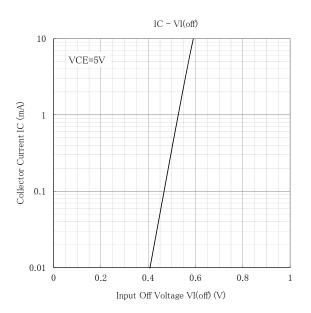
⟨SMALL-SIGNAL TRANSISTOR⟩

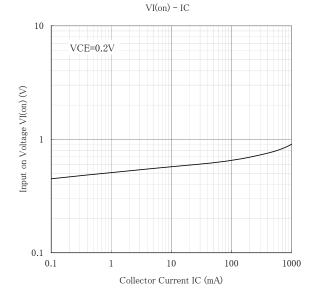
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TRANSISTOR WITH RESISTOR FOR SWITHING APPLICATION SILICON NPN EPITAXIAL TYPE

TYPICAL CHARACTERISTICS







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